

November 2013

FQD20N06

N-Channel QFET® MOSFET

60 V, 16.8 A, 63 mΩ

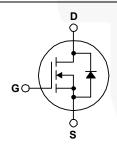
Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- 16.8 A, 60 V, $R_{DS(on)}$ = 63 m Ω (Max.) @ V_{GS} = 10V, I_{D} = 8.4 A
- Low Gate Charge (Typ.11.5 nC)
- · Low Crss (Typ. 25 pF)
- · 100% Avalanche Tested





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FQD20N06	Unit	
V_{DSS}	Drain-Source V	Voltage		60	V	
I _D	Drain Current - Continuous (T _C = 25°C)		C)	16.8	Α	
		- Continuous (T _C = 100°C)		10.6	Α	
I _{DM}	Drain Current	- Pulsed	(Note 1)	67.2	Α	
V _{GSS}	Gate-Source Voltage			± 25	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	155	mJ	
I _{AR}	Avalanche Current		(Note 1)	16.8	Α	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	3.8	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	7.0	V/ns	
P _D	Power Dissipation (T _A = 25°C) *			2.5	W	
_	Power Dissipation (T _C = 25°C) - Derate above 25°C			38	W	
				0.30	W/°C	
T_J , T_{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds			300	°C	

Thermal Characteristics

Symbol	Parameter	FQD20N06TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.28	
В	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD20N06TM	FQD20N06	D-PAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	racteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.07		V/°C
I _{DSS}	Zara Oaka Valla va Dasia Oamaak	V _{DS} = 60 V, V _{GS} = 0 V			1	μА
	Zero Gate Voltage Drain Current	V _{DS} = 48 V, T _C = 125°C			10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 25 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -25 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 8.4 A		0.050	0.063	Ω
9 _{FS}	Forward Transconductance $V_{DS} = 25 \text{ V}, I_D = 8.4 \text{ A}$		\	10		S
Dynami	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		450	590	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		170	220	pF
C _{rss}	Reverse Transfer Capacitance			25	35	pF
Switchi	ng Characteristics					
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, I_{D} = 10 \text{ A},$ $R_{G} = 25 \Omega$		5	20	ns
t _r	Turn-On Rise Time			45	100	ns
t _{d(off)}	Turn-Off Delay Time	116 2032		20	50	ns
t _f	Turn-Off Fall Time	(Note 4)		25	60	ns
Qg	Total Gate Charge	V _{DS} = 48 V, I _D = 20 A,		11.5	15	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V		3		nC
Q _{gd}	Gate-Drain Charge	(Note 4)	/	4.5		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				16.8	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Forward Current			67.2	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 16.8 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _F = 20 A,		43		ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs		50	//	nC

- **Notes:** 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 640 μ H, I_{AS} = 16.8 A, V_{DD} = 25 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} \leq 20 A, di/dt \leq 300 A/ μ s, V_{DD} \leq BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature.

Typical Characteristics

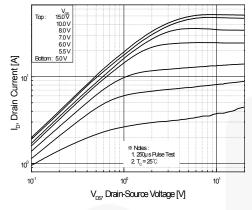


Figure 1. On-Region Characteristics

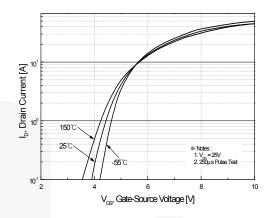


Figure 2. Transfer Characteristics

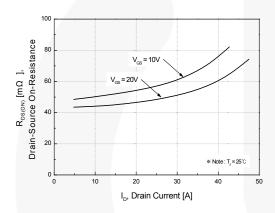


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

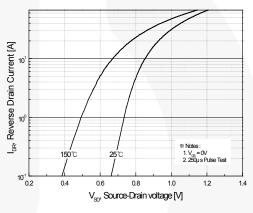


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

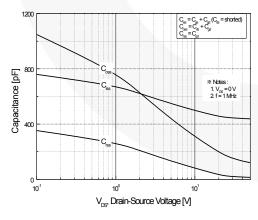


Figure 5. Capacitance Characteristics

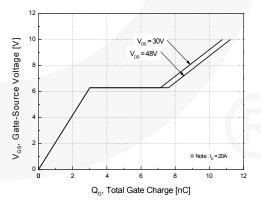


Figure 6. Gate Charge Characteristics

BV_{DSS} (Nomalized (N

0.8 L -100

Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

T,, Junction Temperature [°C]

150

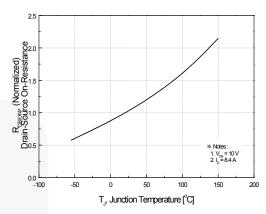


Figure 8. On-Resistance Variation vs. Temperature

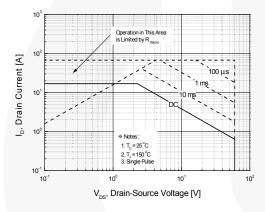


Figure 9. Maximum Safe Operating Area

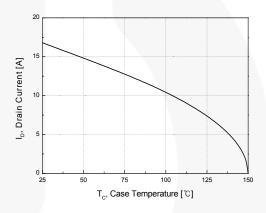


Figure 10. Maximum Drain Current vs. Case Temperature

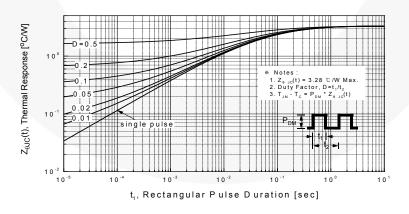


Figure 11. Transient Thermal Response Curve

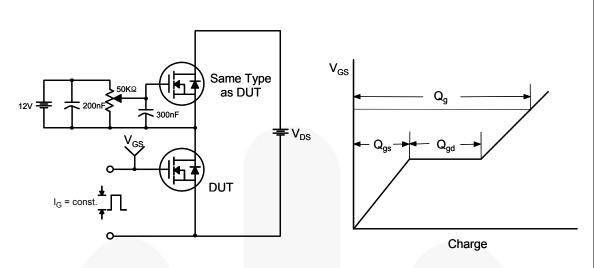


Figure 12. Gate Charge Test Circuit & Waveform

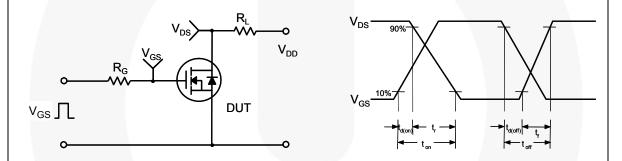


Figure 13. Resistive Switching Test Circuit & Waveforms

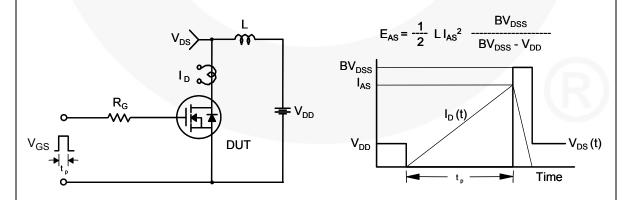
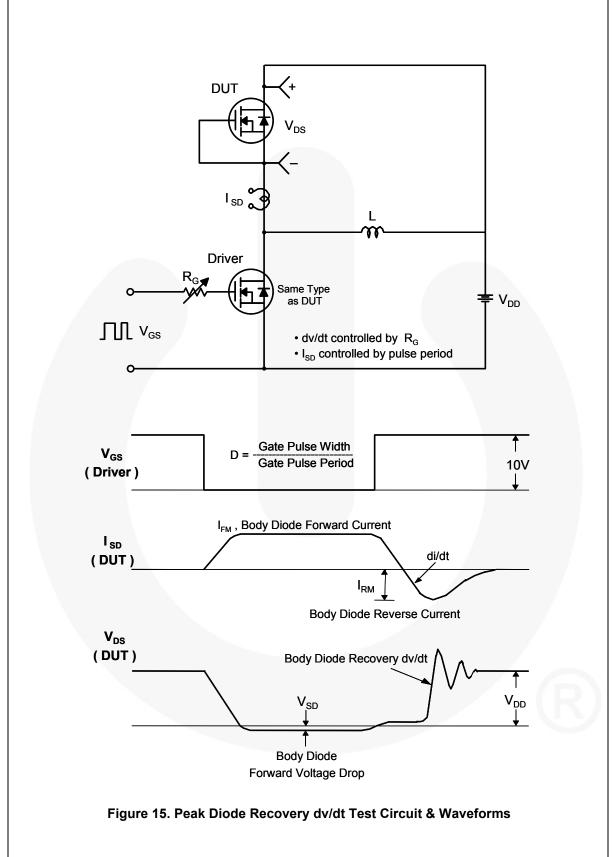


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

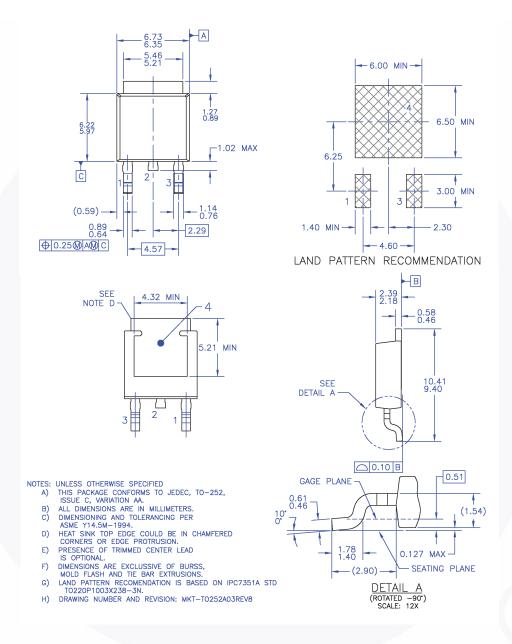


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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